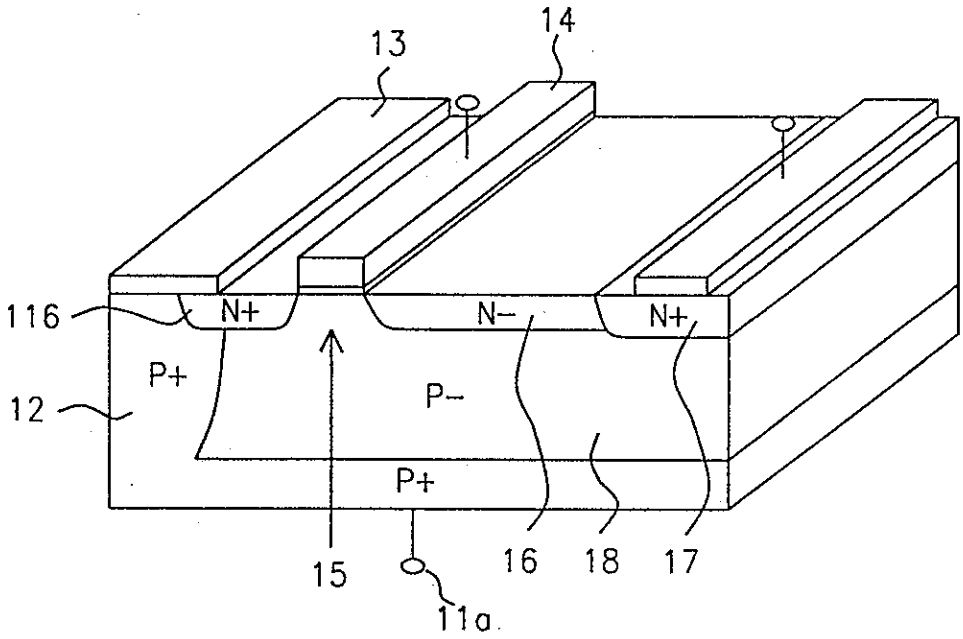


FIG. 1 – Prior Art

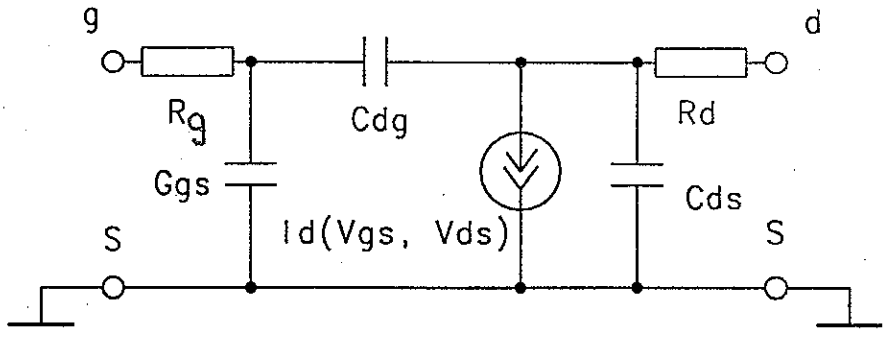


FIG. 2 – Prior Art

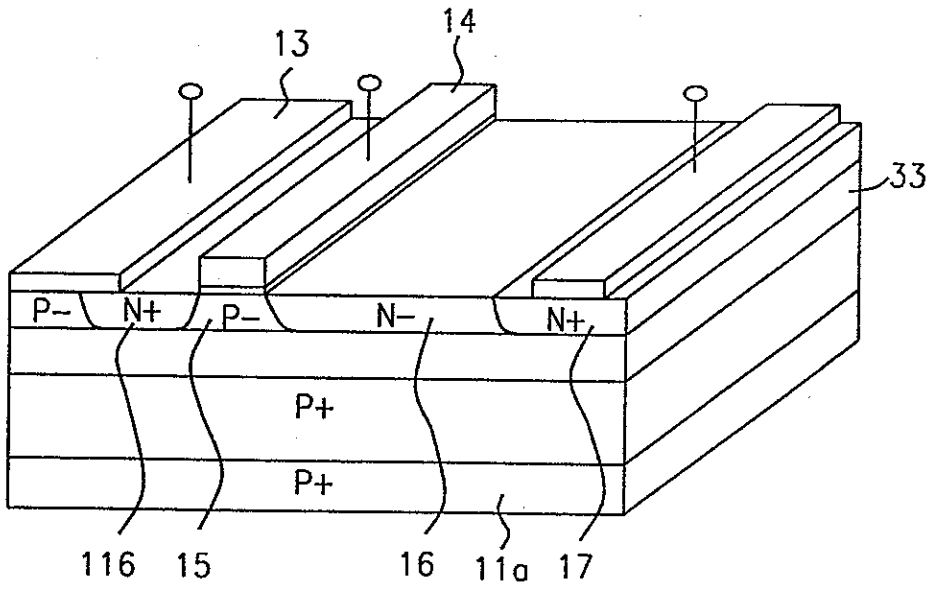


FIG. 3 – Prior Art

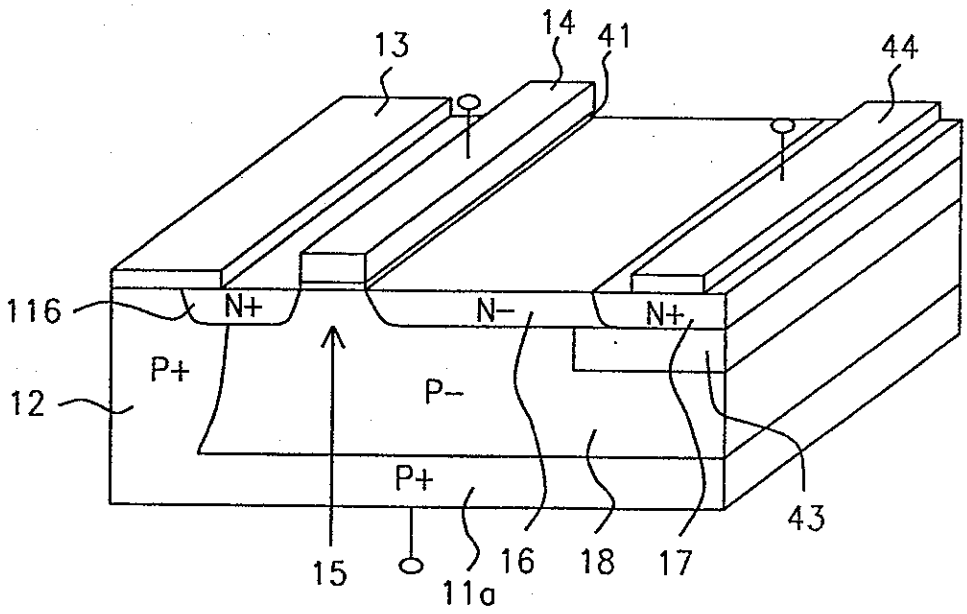


FIG. 4

14 JAN 2005

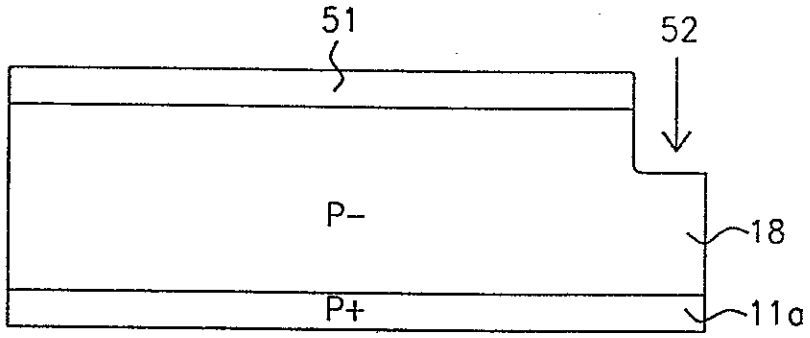


FIG. 5

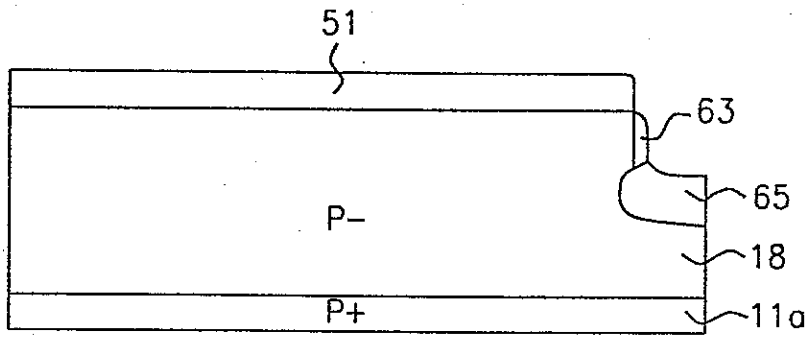


FIG. 6

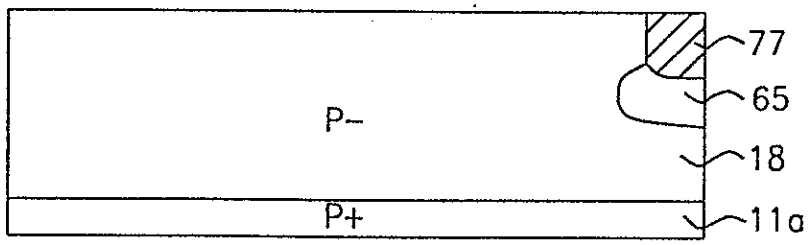


FIG. 7

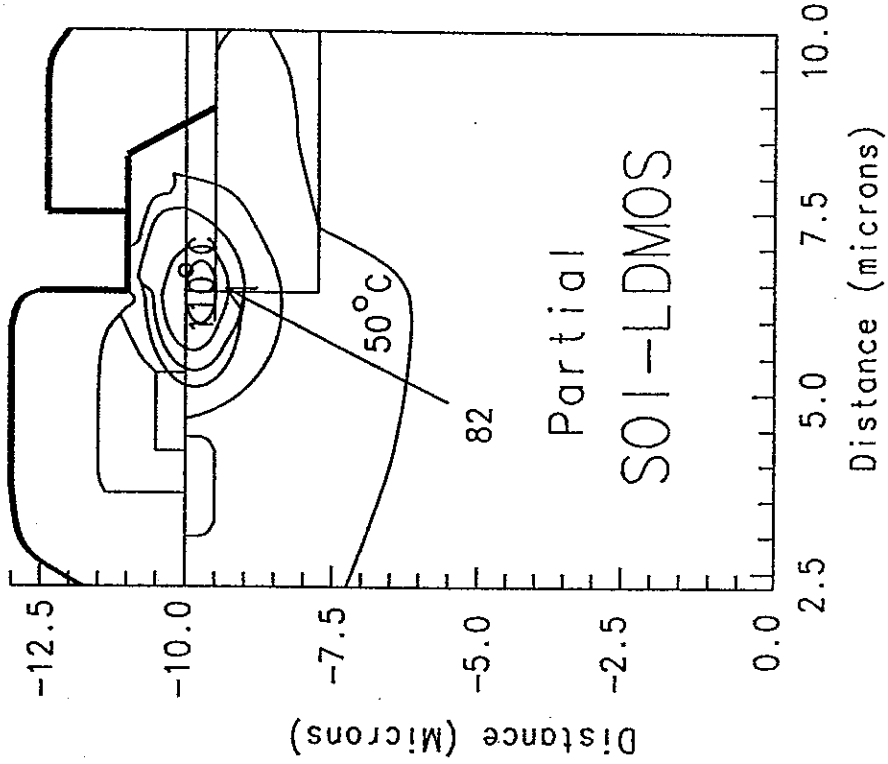

Distance (Microns)
-12.5
-10.0
-7.5
-5.0
-2.5
0.0
2.5
5.0
7.5
10.0
Distance (microns)
SOI-LDMOS
Partial
82
50°C
110°C

FIG. 8b

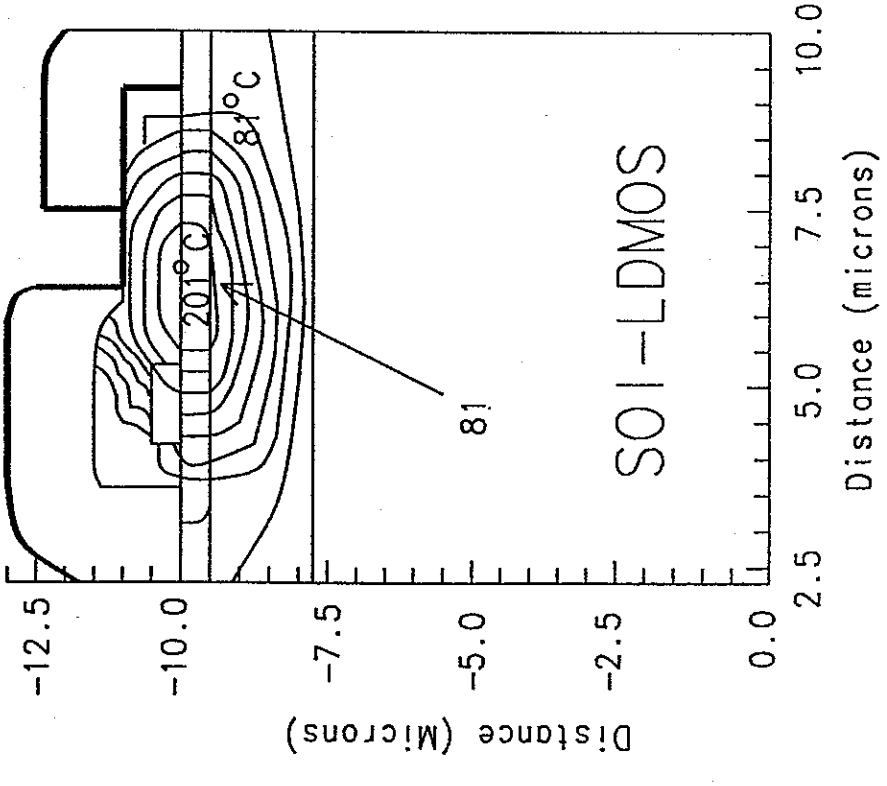

Distance (Microns)
-12.5
-10.0
-7.5
-5.0
-2.5
0.0
2.5
5.0
7.5
10.0
Distance (microns)
SOI-LDMOS
81
84°C
201°C

FIG. 8a

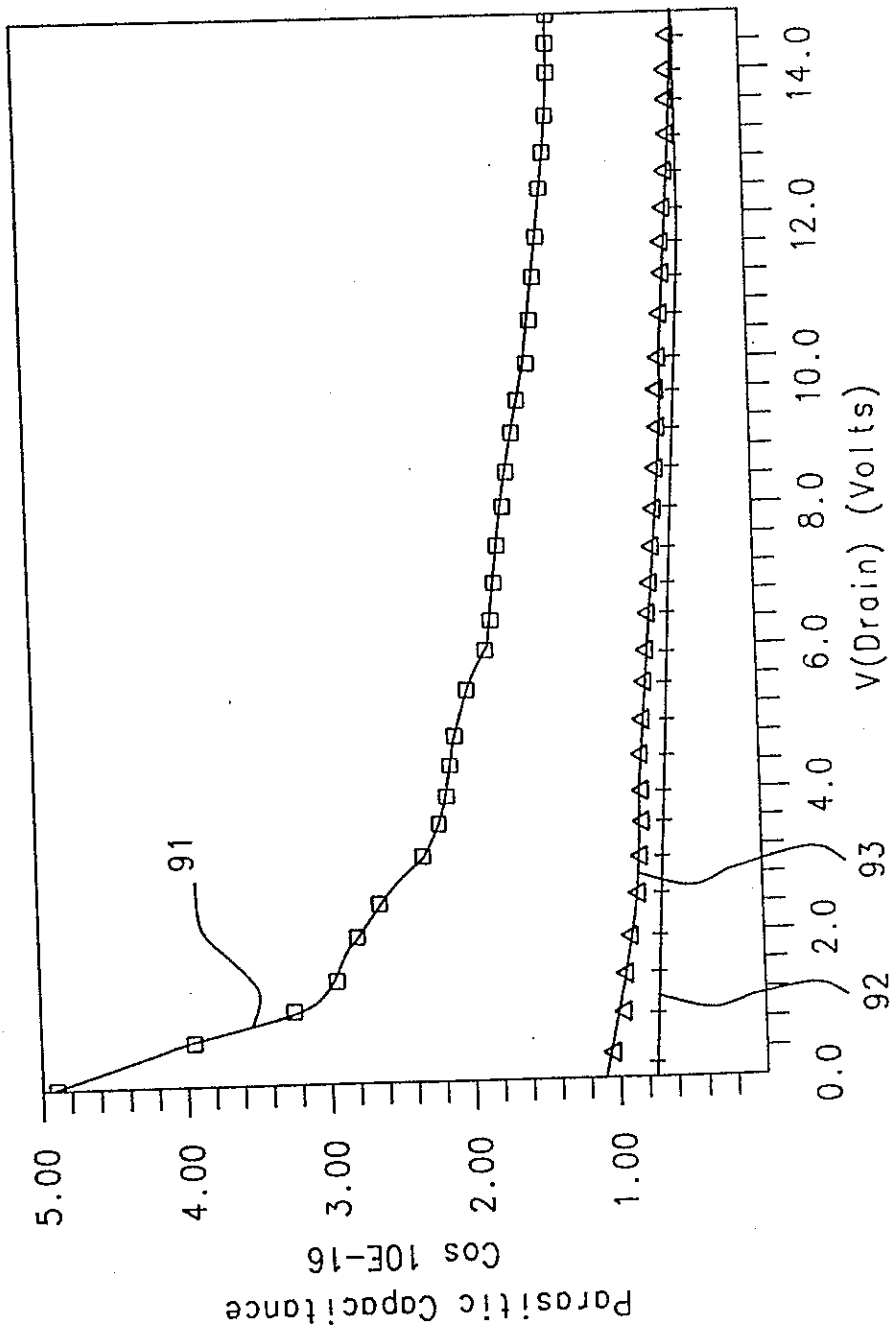

Parasitic Capacitance
Cgs 10E-16
5.00
4.00
3.00
2.00
1.00
0.0
2.0
4.0
6.0
8.0
10.0
12.0
14.0
V(Drain) (Volts)
91
92
93

FIG. 9